

## R-C Thermal Model Parameters

### DESCRIPTION

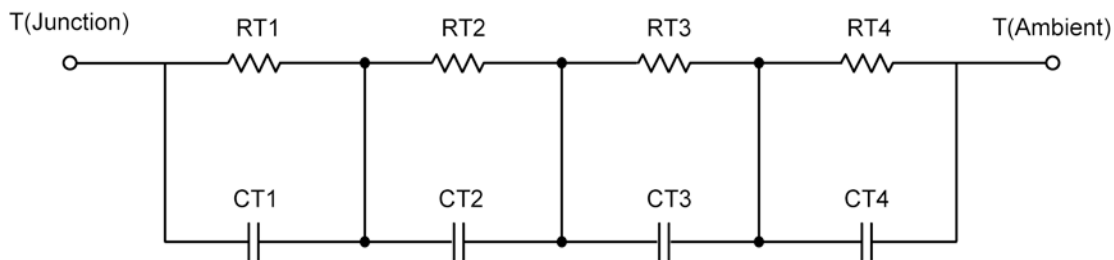
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-Spice, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-Spice Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION

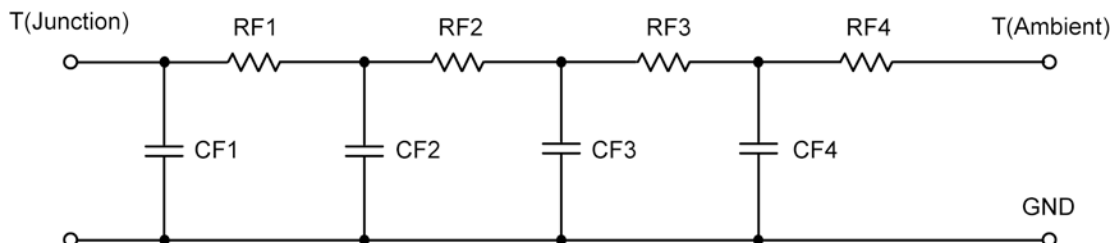


<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	2.4461	793.3107 m	N/A
RT2	8.0131	405.4676 m	N/A
RT3	13.0036	407.3656 m	N/A
RT4	26.5372	193.8561 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	9.1510 m	14.1720 m	N/A
CT2	134.7338 m	3.7300 m	N/A
CT3	2.9027	292.7908 m	N/A
CT4	3.1549	1.8676 m	N/A

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*



## R-C THERMAL MODEL FOR FILTER CONFIGURATION



<b>R-C VALUES FOR FILTER CONFIGURATION</b>			
Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	3.0398	672.5108 m	N/A
RF2	9.0838	111.7113 m	N/A
RF3	31.9999	697.8688 m	N/A
RF4	5.8765	317.9091 m	N/A
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	10.1278 m	1.3056 m	N/A
CF2	124.8509 m	8.3228 m	N/A
CF3	1.4636	5.1364 m	N/A
CF4	8.0543	410.5042 m	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

